

**CPH6526**

Low-Frequency General-Purpose Amplifier Applications

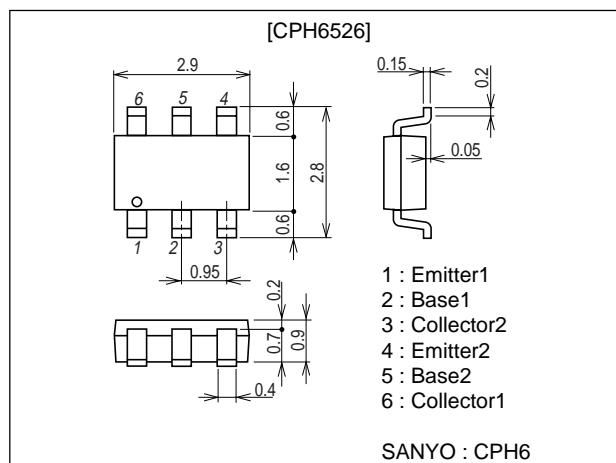
Features

- Composite type with 2 transistors contained in the CPH package currently in use, improving the mounting efficiency greatly.
- The CPH6526 is formed with two chips, being equivalent to the 2SA1622 / 2SC4211, placed in one package.

Package Dimensions

unit : mm

2187



Specifications

() : PNP

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CB0}		(-)55	V
Collector-to-Emitter Voltage	V _{CEO}		(-)50	V
Emitter-to-Base Voltage	V _{EBO}		(-)6	V
Collector Current	I _C		(-)150	mA
Collector Current (Pulse)	I _{CP}		(-)300	mA
Base Current	I _B		(-)30	mA
Collector Dissipation	P _C	1 unit	350	mW
Total Dissipation	P _T		500	mW
Junction Temperature	T _J		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CB0}	V _{CB} =(-)35V, I _E =0			(-)0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(-)0.1	μA
DC Current Gain	h _{FE}	V _{CE} =(-)6V, I _C =(-)1mA	160		600	

Marking : 3R

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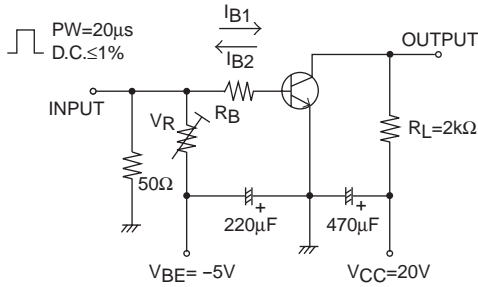
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)6V, I_C=(-)10mA$		(180)200		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)6V, f=1MHz$		(2.9)1.7		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)50mA, I_B=(-)5mA$		(-0.11)0.08	(-)0.4	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)50mA, I_B=(-)5mA$		(-)0.8	(-)1.0	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)55			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-)6			V
Turn ON Time	t_{on}	See specified Test Circuit.		0.15		μs
Storage Time	t_{stg}	See specified Test Circuit.		(0.60)0.75		μs
Fall Time	t_f	See specified Test Circuit.		0.20		μs

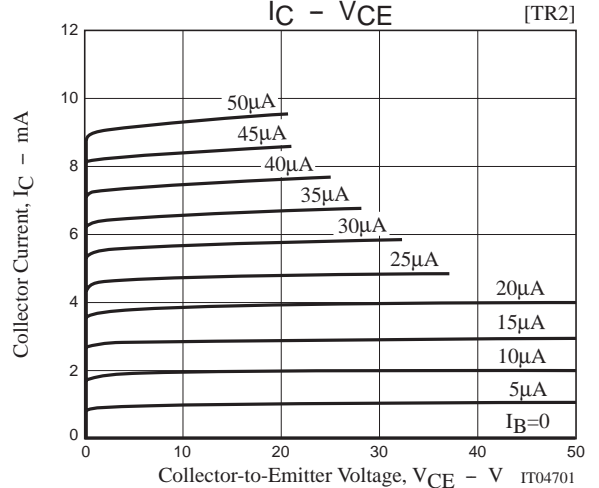
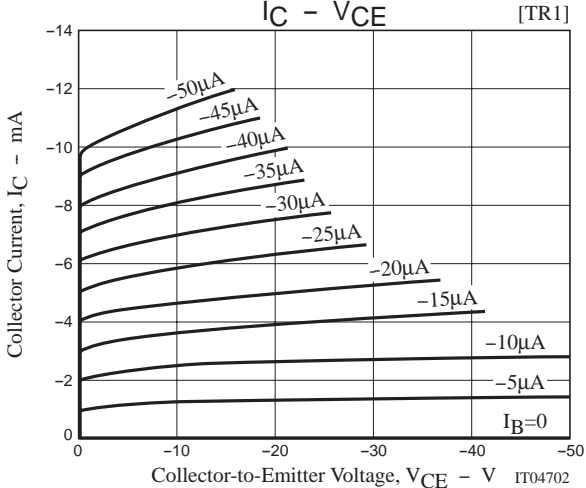
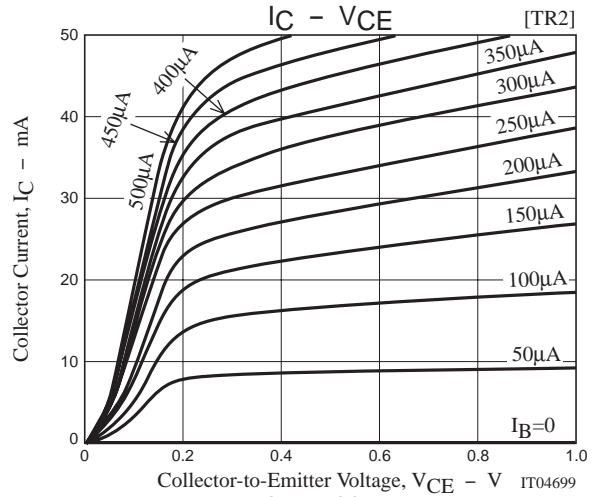
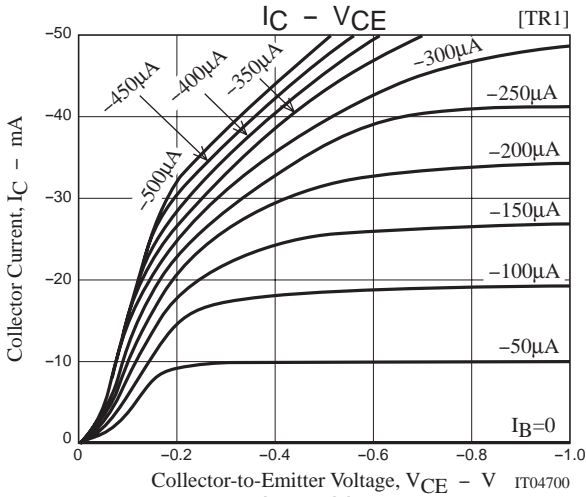
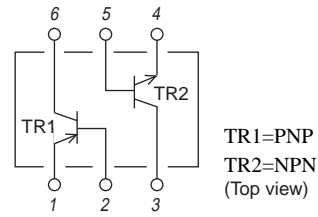
Note : The specifications shown above are for each individual transistor.

Switching Time Test Circuit

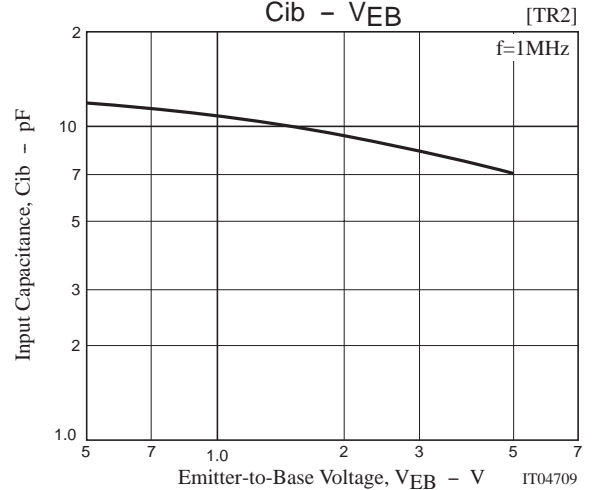
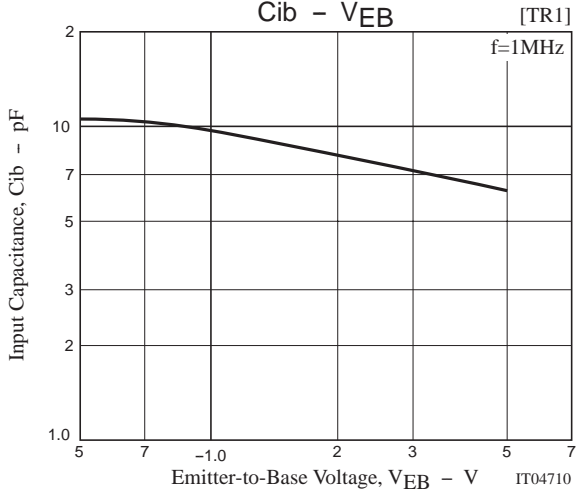
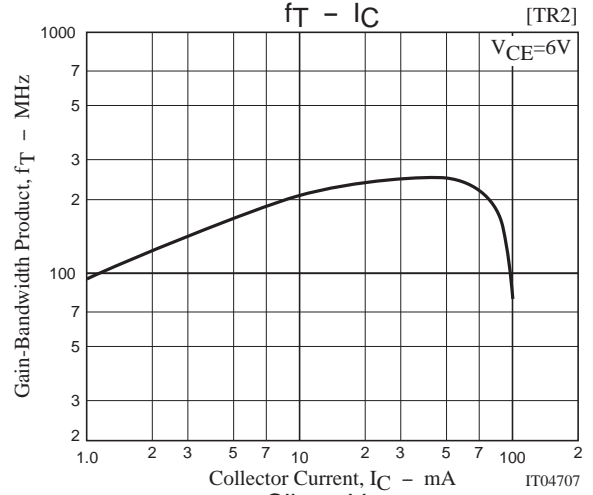
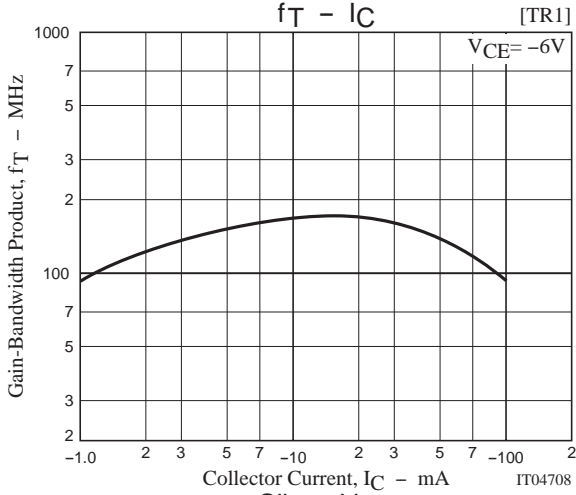
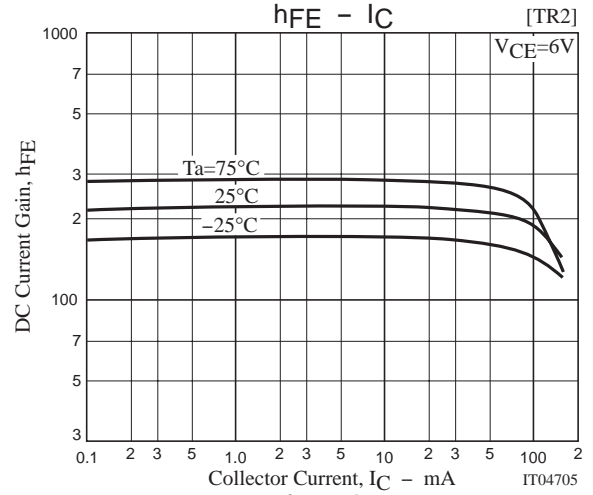
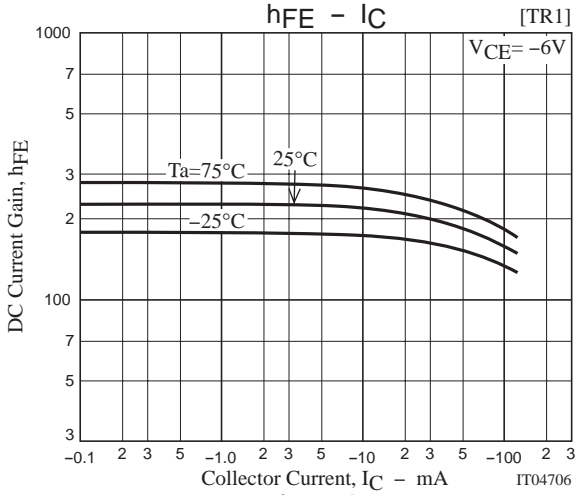
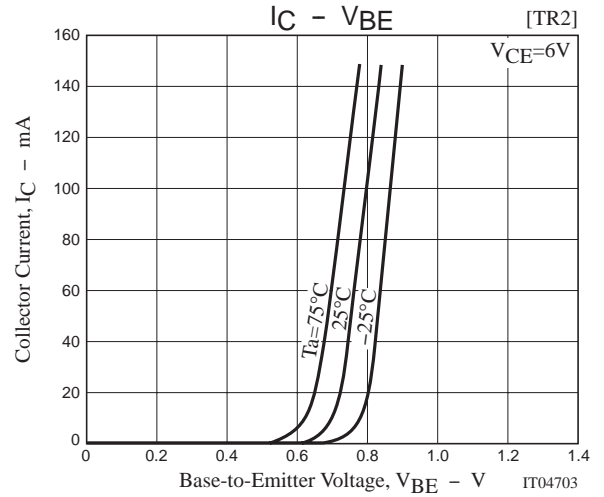
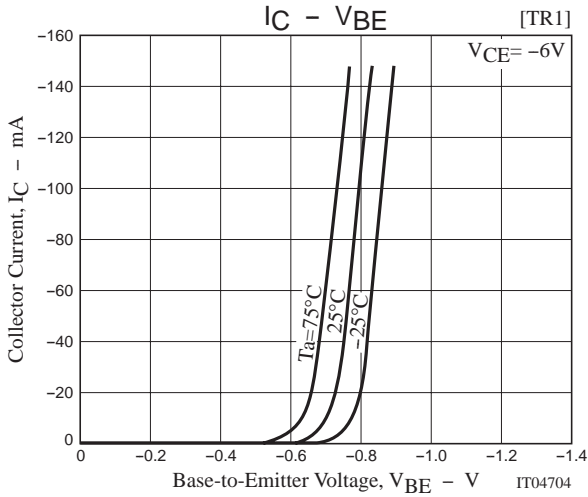


$I_C=10I_{B1} = -10I_{B2}=10mA$
For PNP, the polarity is reversed.

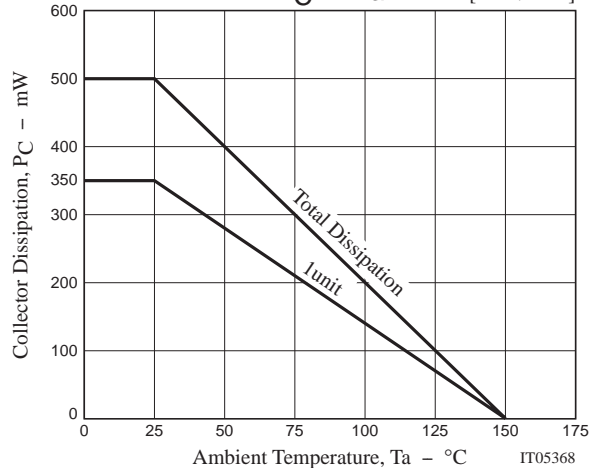
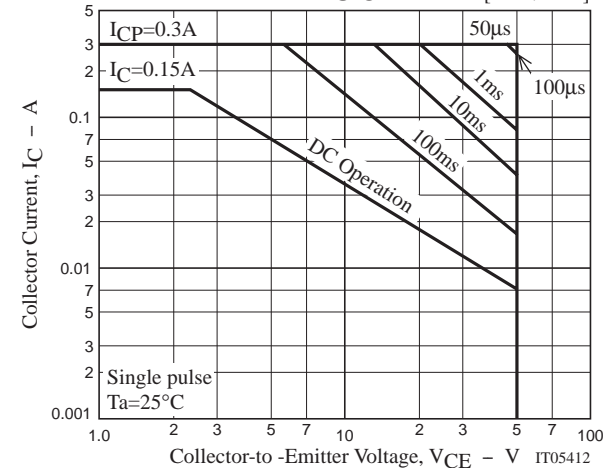
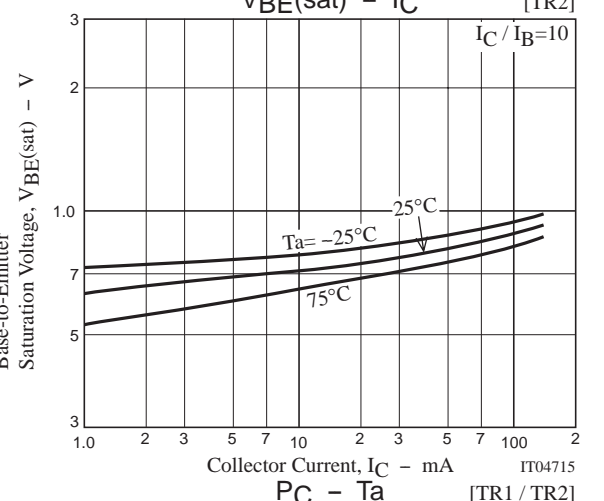
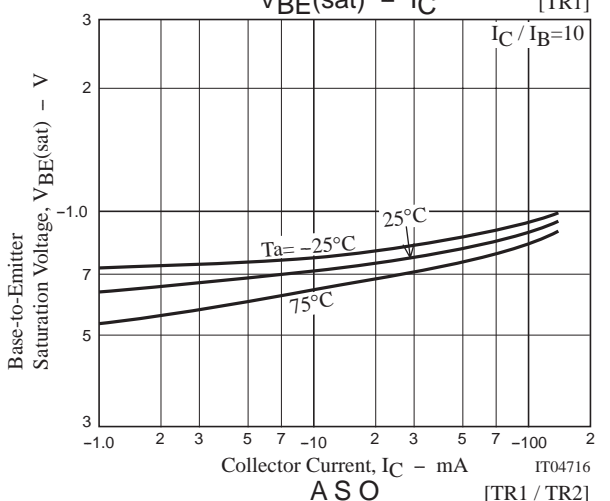
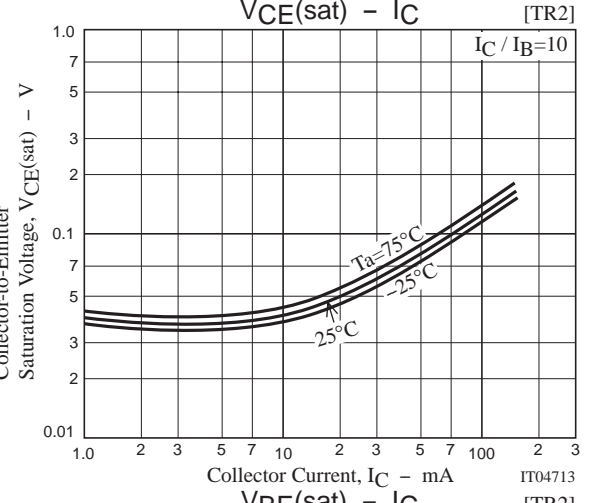
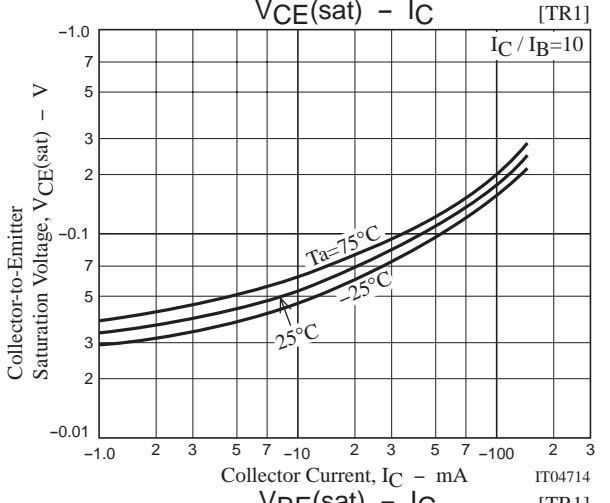
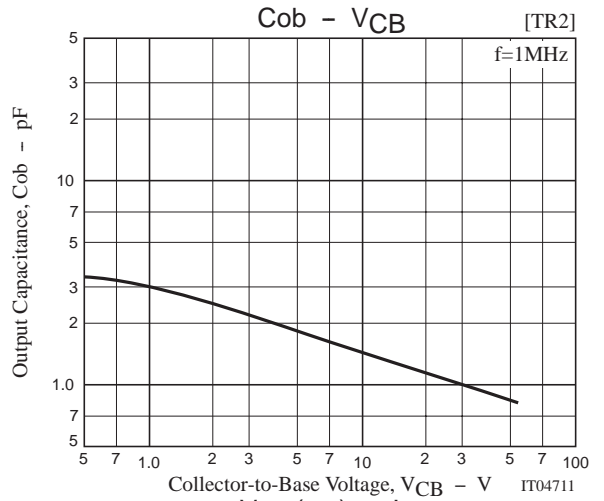
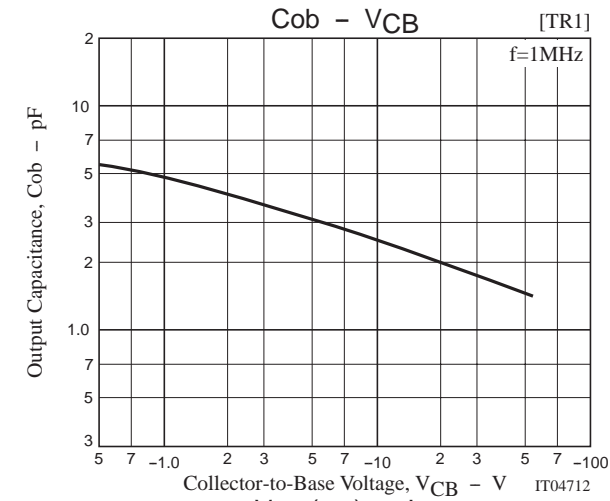
Electrical Connection



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